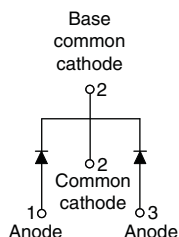


Hyperfast Rectifier, 2 x 10 A FRED Pt®



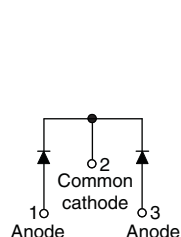
TO-220AB



VS-20CTH03PbF



TO-220 FULL-PAK



VS-20CTH03FPPbF

FEATURES

- Hyperfast recovery time
- Low forward voltage drop
- 175 °C operating junction temperature
- Low leakage current
- Fully isolated package ($V_{INS} = 2500 V_{RMS}$)
- UL E78996 pending
- Compliant to RoHS Directive 2002/95/EC
- AEC-Q101 qualified (TO-220)
- Designed and qualified for industrial level (TO-220FP)



RoHS
COMPLIANT

DESCRIPTION/APPLICATIONS

300 V series are the state of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop and hyperfast recovery time.

The planar structure and the platinum doped life time control, guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, UPS, DC/DC converters as well as freewheeling diodes in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

PRODUCT SUMMARY

Package	TO-220AB, TO-220FP
$I_{F(AV)}$	2 x 10 A
V_R	300 V
V_F at I_F	1.25 V
t_{rr} typ.	See Recovery table
T_J max.	175 °C
Diode variation	Common cathode

ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Peak repetitive reverse voltage	V_{RRM}		300	V
Average rectified forward current	$I_{F(AV)}$	$T_C = 160\text{ °C}$	10	A
		$T_C = 135\text{ °C}$	20	
			120	
Non-repetitive peak surge current	I_{FSM}	$T_J = 25\text{ °C}$	120	
Operating junction and storage temperatures	T_J, T_{Stg}		- 65 to 175	°C

ELECTRICAL SPECIFICATIONS ($T_J = 25\text{ °C}$ unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Breakdown voltage, blocking voltage	V_{BR}, V_R	$I_R = 100\text{ }\mu A$	300	-	-	V
Forward voltage	V_F	$I_F = 10\text{ A}$	-	1.05	1.25	
		$I_F = 10\text{ A}, T_J = 125\text{ °C}$	-	0.85	0.95	
Reverse leakage current	I_R	$V_R = V_R$ rated	-	-	20	μA
		$T_J = 125\text{ °C}, V_R = V_R$ rated	-	6	200	
Junction capacitance	C_T	$V_R = 300\text{ V}$	-	30	-	pF
Series inductance	L_S	Measured lead to lead 5 mm from package body	-	8	-	nH

DYNAMIC RECOVERY CHARACTERISTICS ($T_C = 25\text{ }^{\circ}\text{C}$ unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Reverse recovery time	t_{rr}	$I_F = 1\text{ A}$, $dI_F/dt = 50\text{ A}/\mu\text{s}$, $V_R = 30\text{ V}$	-	-	35	ns
		$I_F = 1\text{ A}$, $dI_F/dt = 100\text{ A}/\mu\text{s}$, $V_R = 30\text{ V}$	-	-	30	
		$T_J = 25\text{ }^{\circ}\text{C}$	-	31	-	
		$T_J = 125\text{ }^{\circ}\text{C}$	-	42	-	
Peak recovery current	I_{RRM}	$T_J = 25\text{ }^{\circ}\text{C}$	-	2.4	-	A
		$T_J = 125\text{ }^{\circ}\text{C}$	-	5.6	-	
Reverse recovery charge	Q_{rr}	$T_J = 25\text{ }^{\circ}\text{C}$	-	36	-	nC
		$T_J = 125\text{ }^{\circ}\text{C}$	-	120	-	

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDCTIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T _J , T _{Stg}		- 65	-	175	°C
Thermal resistance, _____ per diode junction to case (FULL-PAK) per diode	R _{thJC}	Mounting surface, flat, smooth and greased	-	-	1.5	°C/W
			-	-	3.9	
Marking device		Case style TO-220AB	20CTH03			
		Case style TO-220 FULL-PAK	20CTH03FP			

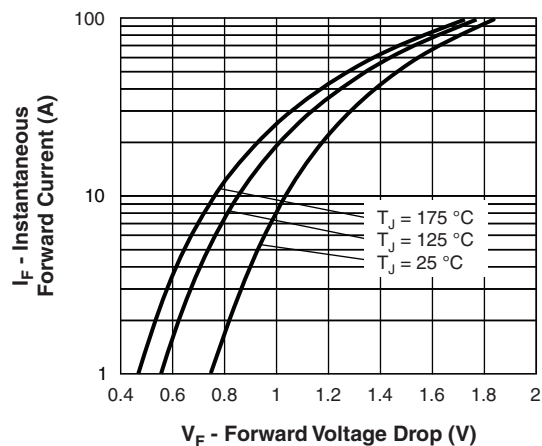


Fig. 1 - Typical Forward Voltage Drop Characteristics

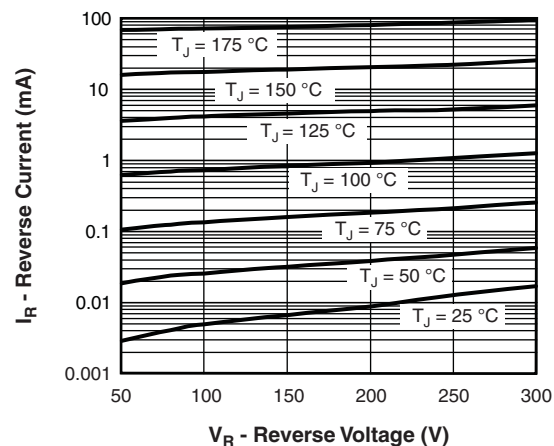


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage



VS-20CTH03PbF, VS-20CTH03FPPbF

Hyperfast Rectifier, 2 x 10 A FRED Pt® Vishay Semiconductors

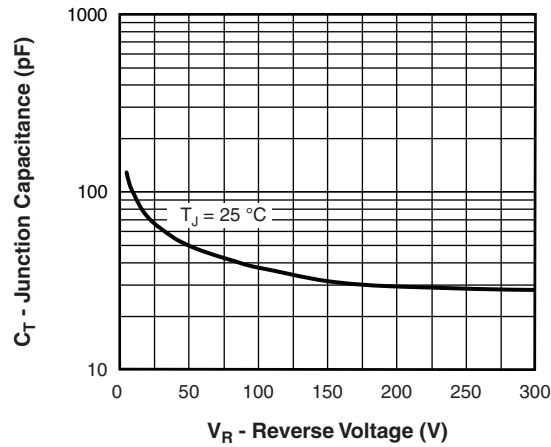


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

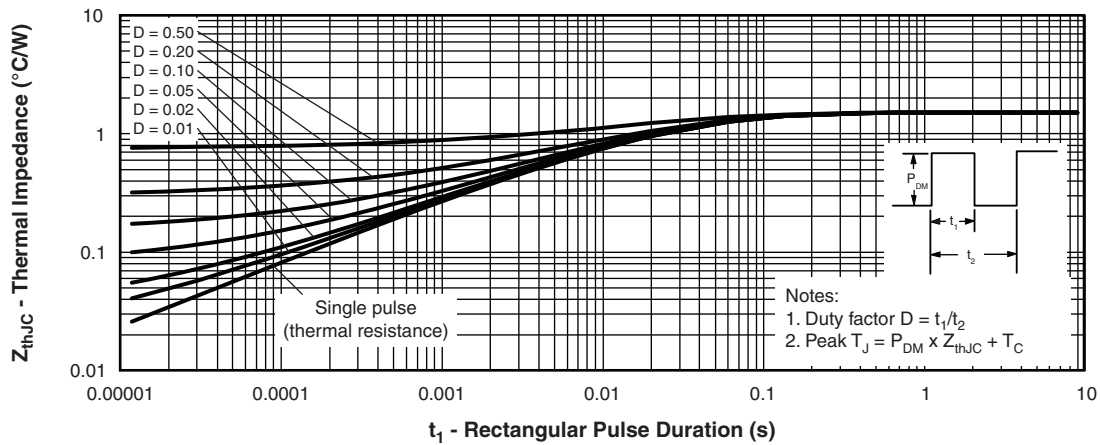


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

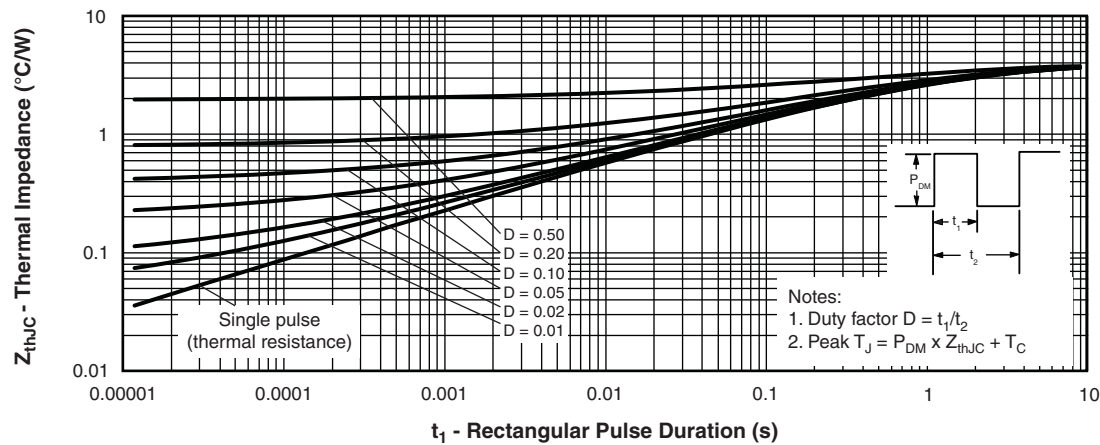


Fig. 5 - Maximum Thermal Impedance Z_{thJC} Characteristics (FULL-PAK)

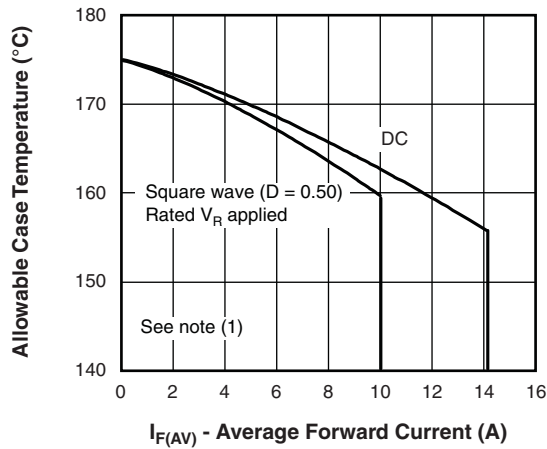


Fig. 6 - Maximum Allowable Case Temperature vs. Average Forward Current

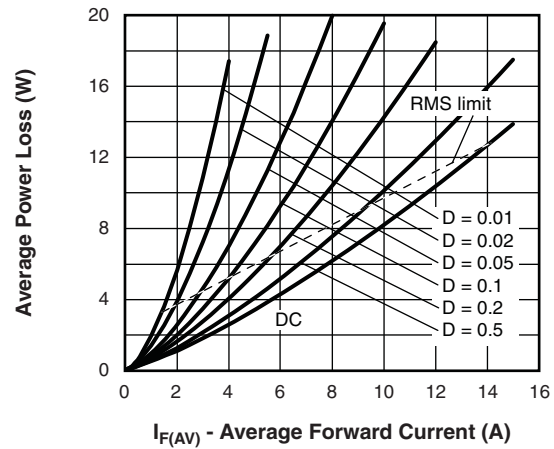


Fig. 8 - Forward Power Loss Characteristics

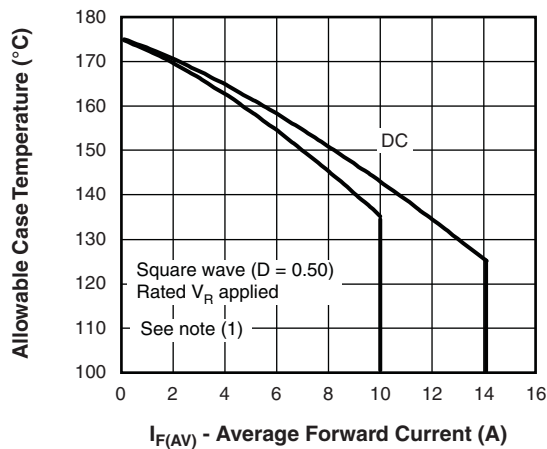


Fig. 7 - Maximum Allowable Case Temperature vs. Average Forward Current (FULL-PAK)

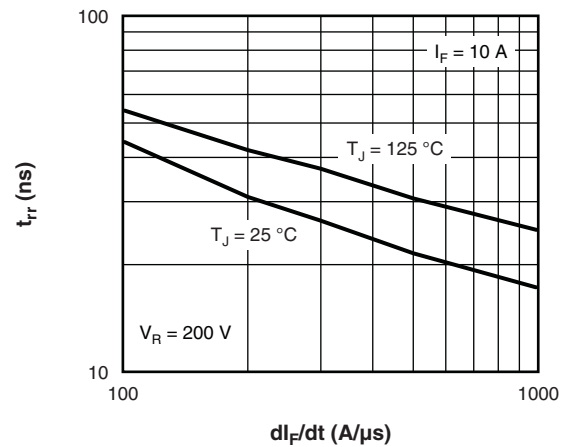


Fig. 9 - Typical Reverse Recovery Time vs. dI_F/dt

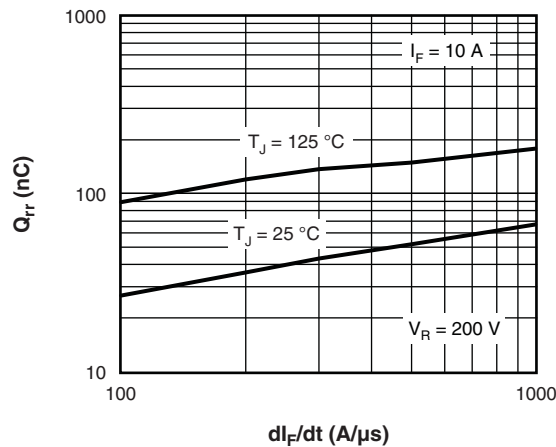


Fig. 10 - Typical Stored Charge vs. dI_F/dt

Note

- (1) Formula used: $T_C = T_J - (P_d + P_{dREV}) \times R_{thJC}$
 P_d = Forward power loss = $I_{F(AV)} \times V_{FM}$ at $(I_{F(AV)}/D)$ (see fig. 8);
 P_{dREV} = Inverse power loss = $V_{R1} \times I_R (1 - D)$; I_R at V_{R1} = Rated V_R

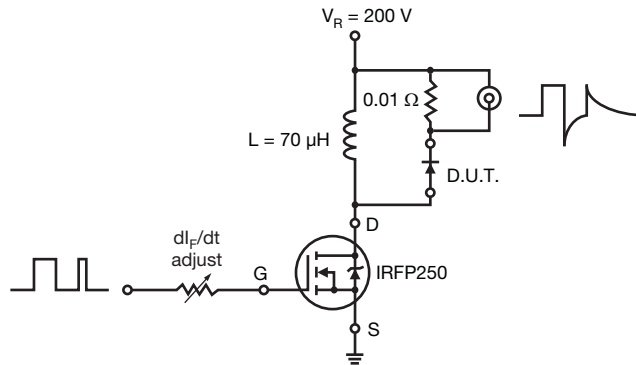


Fig. 11 - Reverse Recovery Parameter Test Circuit

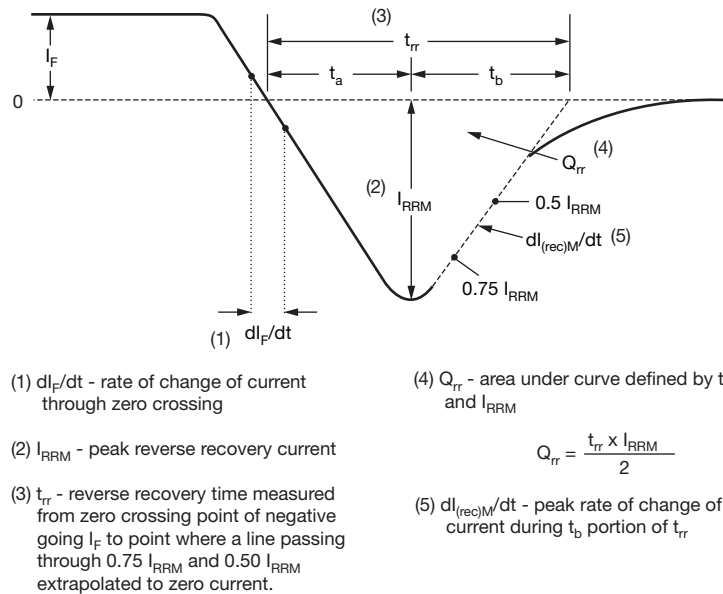


Fig. 12 - Reverse Recovery Waveform and Definitions

VS-20CTH03PbF, VS-20CTH03FPPbF

Vishay Semiconductors Hyperfast Rectifier, 2 x 10 A FRED Pt®



ORDERING INFORMATION TABLE

Device code	VS-	20	C	T	H	03	FP	PbF
	1	2	3	4	5	6	7	8

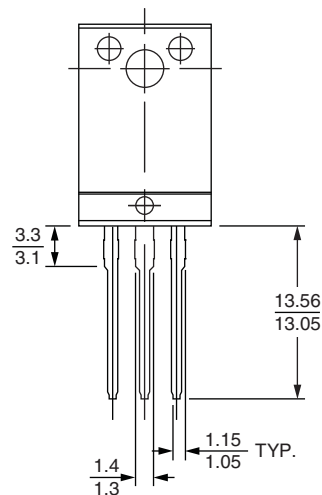
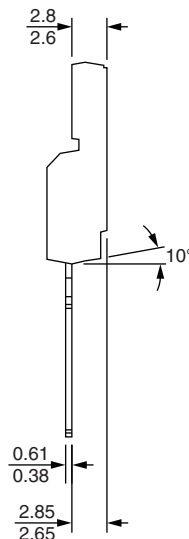
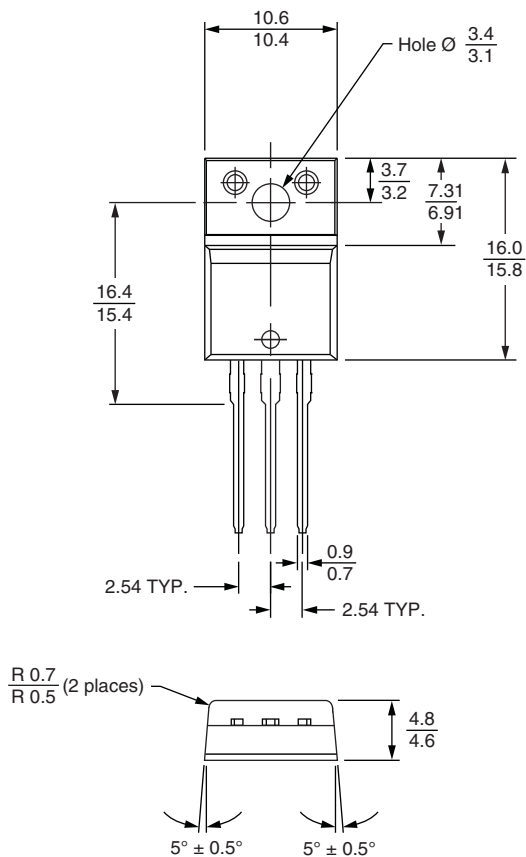
- 1** - Vishay Semiconductors product
- 2** - Current rating (20 = 20 A)
- 3** - C = Common cathode
- 4** - T = TO-220, D²PAK
- 5** - H = Hyperfast recovery
- 6** - Voltage rating (03 = 300 V)
- 7** -
 - None = TO-220AB
 - FP = TO-220 FULL-PAK
- 8** - PbF = Lead (Pb)-free

Tube standard pack quantity: 50 pieces

LINKS TO RELATED DOCUMENTS		
Dimensions	TO-220AB	www.vishay.com/doc?95222
	TO-220AB FULL-PAK	www.vishay.com/doc?95072
Part marking information	TO-220AB	www.vishay.com/doc?95225
	TO-220AB FULL-PAK	www.vishay.com/doc?95069



DIMENSIONS in millimeters



Lead assignments

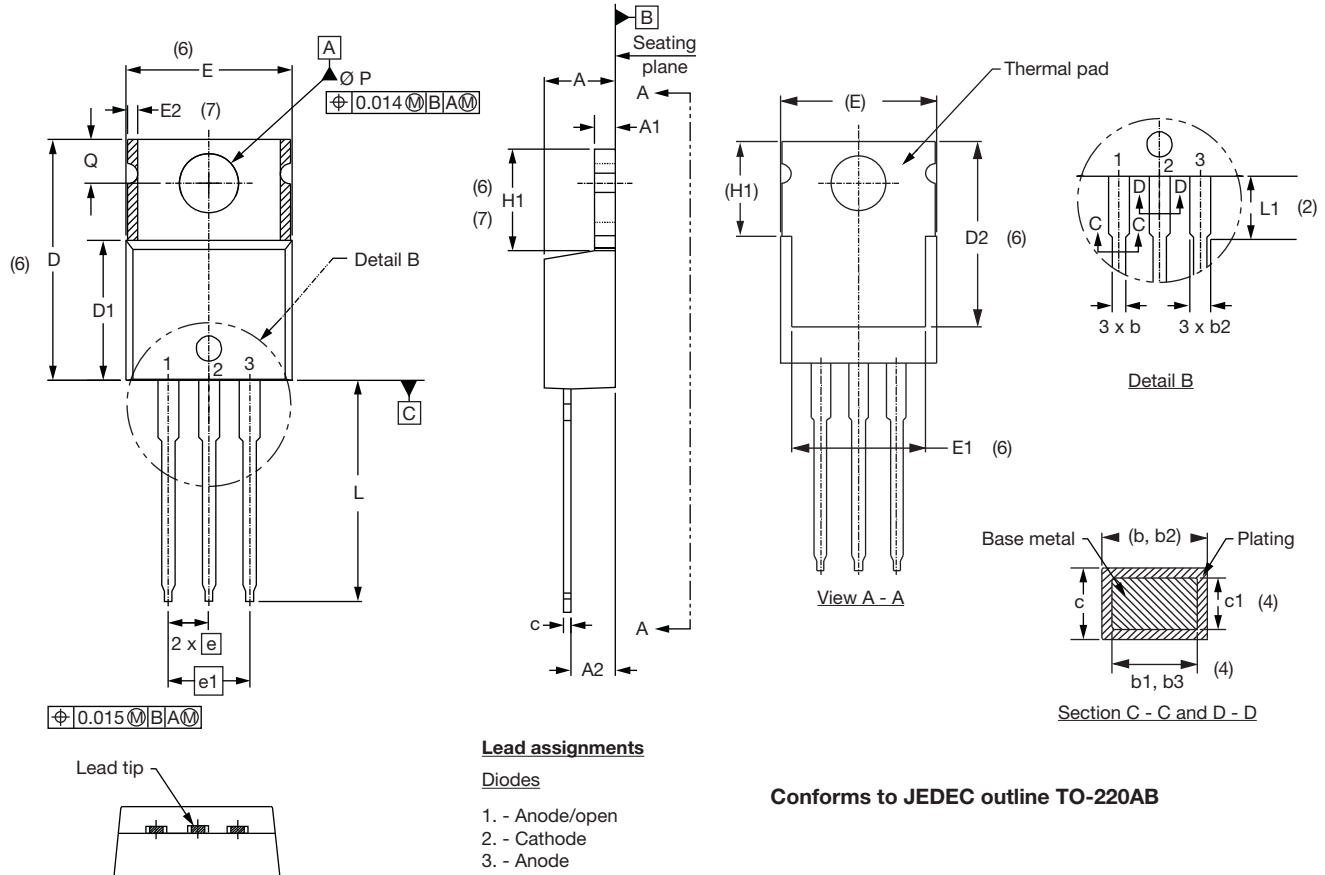
Diodes

1. - Anode/open
2. - Cathode
3. - Anode

Conforms to JEDEC outline TO-220 FULL-PAK

TO-220AB

DIMENSIONS in millimeters and inches



SYMBOL	MILLIMETERS		INCHES		NOTES
	MIN.	MAX.	MIN.	MAX.	
A	4.25	4.65	0.167	0.183	
A1	1.14	1.40	0.045	0.055	
A2	2.56	2.92	0.101	0.115	
b	0.69	1.01	0.027	0.040	
b1	0.38	0.97	0.015	0.038	4
b2	1.20	1.73	0.047	0.068	
b3	1.14	1.73	0.045	0.068	4
c	0.36	0.61	0.014	0.024	
c1	0.36	0.56	0.014	0.022	4
D	14.85	15.25	0.585	0.600	3
D1	8.38	9.02	0.330	0.355	
D2	11.68	12.88	0.460	0.507	6

SYMBOL	MILLIMETERS		INCHES		NOTES
	MIN.	MAX.	MIN.	MAX.	
E	10.11	10.51	0.398	0.414	3, 6
E1	6.86	8.89	0.270	0.350	6
E2	-	0.76	-	0.030	7
e	2.41	2.67	0.095	0.105	
e1	4.88	5.28	0.192	0.208	
H1	6.09	6.48	0.240	0.255	6, 7
L	13.52	14.02	0.532	0.552	
L1	3.32	3.82	0.131	0.150	2
Ø P	3.54	3.73	0.139	0.147	
Q	2.60	3.00	0.102	0.118	
θ	90° to 93°		90° to 93°		

Notes

- (1) Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Lead dimension and finish uncontrolled in L1
- (3) Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Dimension b1, b3 and c1 apply to base metal only
- (5) Controlling dimensions: inches
- (6) Thermal pad contour optional within dimensions E, H1, D2 and E1
- (7) Dimensions E2 x H1 define a zone where stamping and singulation irregularities are allowed
- (8) Outline conforms to JEDEC TO-220, except A2 (maximum) and D2 (minimum) where dimensions are derived from the actual package outline



Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and/or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk and agree to fully indemnify and hold Vishay and its distributors harmless from and against any and all claims, liabilities, expenses and damages arising or resulting in connection with such use or sale, including attorneys fees, even if such claim alleges that Vishay or its distributor was negligent regarding the design or manufacture of the part. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.

Данный компонент на территории Российской Федерации

Вы можете приобрести в компании MosChip.

Для оперативного оформления запроса Вам необходимо перейти по данной ссылке:

<http://moschip.ru/get-element>

Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

Skype отдела продаж:

moschip.ru

moschip.ru_4

moschip.ru_6

moschip.ru_9